VACUUMSCHMELZE	SPECIFICAT	ION	Item no.:		T60404-N4646-X412	
K-No.: 24618	50/100A Current Sensor For the electronic measurement of DC, AC, pulsed, mixed, with a g Isolation between the primary circu (high power) and the secondary ci (electronic circuit)	f currents: Jalvanic Jit rcuit			Date: 20	.01.2022
Customer: Stan	dard type	Customers Part	no.:		Page 1	of 4
 Description Closed loop (comp Current Sensor wit field probe Printed circuit boar Casing and material 	 Closed loop (compensation) Current Sensor with magnetic field probe Printed circuit board mounting Casing and materials UL-listed Excellent accuracy Very low offset current Very low temperature dependency and current drift Very low hysteresis of offset current Low response time Wide frequency bandwidth Compact design Reduced offset ripple 		App Main appli offset	 Applications Mainly used for stationary operation in industrial applications: AC variable speed drives and servo motor drives Static converters for DC motor drives Battery supplied applications Switched Mode Power Supplies (SMPS) Power Supplies for welding applications Uninterruptable Power Supplies (UPS) 		
Electrical data – R	atings					
Ipn Rm Isn Kn	Primary nominal rms current @ $V_C = \pm 15V$, $R_M \ge 0\Omega$ @ $V_C = \pm 12V$, $R_M \ge 0\Omega$ or $V_C =$ Measuring resistance $V_{C}=\pm 12V$ $V_{C}=\pm 15V$ Secondary nominal rms current Turns ratio	±15V, R _M ≥ 16Ω ⁄			50 100 0 200 16 400 25/50 13 : 2000	A A Ω Ω mA
<u>Accuracy – Dynan</u>	nic performance data		min.	tvp.	max.	Unit
IP,max	Max. measuring range @ V _C = ±12V, R _M = 10 Ω (t _{max} = @ V _C = ±15V, R _M = 16 Ω (t _{max} =	10sec) 10sec)	±145 ±175	0.1	0.5	A A
X	Accuracy @ I_{PN} , $I_A = 25^{\circ}C$ Linearity			0.1	0.5	%
lo	Offset current @ IP=0, TA= 25°C)		0.02	0.08	mA
tr	Response time			500		ns
Δt (I _{P,max}) f	Delay time at di/dt = 100 A/ μ s Frequency bandwidth		DC200	200		ns kHz
General data						
Ŧ			min.	typ.	max.	Unit
TA	Ambient storage temperature (a	cc M3101)	-40		+00	°C
m	Mass		10	13.5	100	g
Vc	Supply voltage		±11.4	±12 or ±15	±15.75	V
lc	Current consumption			18.5		mA
0	Constructed and manufactored Reinforced insulation, Insulation	and tested in accord material group 1, F	dance with E Pollution deg	EN 61800-5-1 jree 2	(Pin 1 - 6 to Pin	7 – 9)
Screen	Creepage (component without solo	ler pad)	10.2			mm
V _{sys}	System voltage overvoltage c	ategory 3	10.L		600	V _{RMS}
Vwork	Working voltage (table 7 acc	. to EN61800-5-1)			1020	VRMS
Upd	Rated discharge voltage				1400	VPEAK
Max. potential c	ifference acc. to UL 508		RMS		600	VAC
Date Name I 20.01.2022 NSch. 21.01.10 D.1	suue Amendment 81 Applicable documents on sheet 81 Page 2: Marking abanged from	4 changed. "The color	r of the plastic	material add	ded. Minor chang	e
Hrsg.: R&D-PD NF	I D Bearb: DJ	MC-PM: NSch.	12. Faye 3, I		+ accurately defil	g.: SB
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-No.: 24618 Eustomer: Stan Iectrical Data (inv V _{Ctot} R _s R _p X _{Ti}	50/100A Curre For the electronic r DC, AC, pulsed, m Isolation between t (high power) and th (electronic circuit) dard type restigate by a type c Maximum supply ±15.75 to ±18 V: f	nt Sensor neasurement of currents: ixed, with a galvanic he primary circuit ne secondary circuit Customers Pa			Date:	20.01.2022	
Customer: Stan lectrical Data (inv V _{Ctot} Rs R _p X _{Ti}	dard type restigate by a type c Maximum supply ±15.75 to ±18 V: f	Customers P				Date: 20.01.2022	
lectrical Data (inv V _{Ctot} R _S R _p X _{Ti}	Areastigate by a type c Maximum supply ±15.75 to ±18 V: f	hecking)	art no.:		Page	3 of 4	
V _{Ctot} Rs Rp X _{Ti}	Maximum supply ±15.75 to ±18 V: f	neoking/					
V _{Ctot} Rs R _p X _{Ti}	Maximum supply ±15.75 to ±18 V: f		min.	typ.	max.	Unit	
Rs Rp X _{Ti}		voltage (without function) or 1s per hour			±18	V	
R _p X _{Ti}	Secondary coil re	sistance @ T _A =85°C			145	Ω	
X _{Ti}	Primary coil resist	ance per turn @ T _A =25°C			0.36	mΩ	
1	Temperature drift	of X @ T _A = -40 +85°C			0.1	%	
Oges	Offset current (inc	luding I ₀ , I _{0t} , I _{0T})			0.1	mA	
Ot	Long term drift Of	fset current I ₀		0.03		mA	
от	Offset current tem	perature drift $I_0 @ T_A = -40 \dots$	-85°C	0.03		mA	
н	Hyteresis current	@ I _P =0 (caused by primary curre	nt 3 x I _{PN})	0.02	0.05	mA	
$10/\Delta V_{C}$	Supply voltage rej	ection ratio			0.01	mA/V	
DSS	Offsetripple (with	1MHz- filter first order)			0.15	mA	
OSS	Offsetripple (with	100kHz- filter first order)		0.017	0.025	mA	
DSS	Offsetripple (with	20kHz- filter first order)		0.005	0.007	mA	
k	Maximum possible	e coupling capacity (primary –	secondary)	5		pF	
	accelerates the aging p	process of the sensor.	Unage				
spection (Measu	ement after temperature	e balance of the samples at room	emperature; S	C = significan	t characteristic)		
<mark>spection</mark> (Measu ≺N(SC) (V)	ement after temperature M3011/6	e balance of the samples at room Transformation ratio (IP=3*	temperature; S 10A, 40-80 F	C = significan Iz)	t characteristic) 13 : 2000	0±0.5 %	
spection (Measu K _N (SC) (V) 0 (V)	ement after temperature M3011/6 M3226	e balance of the samples at room Transformation ratio (IP=3* Offset current	temperature; S 10A, 40-80 F	C = significan Iz)	t characteristic) 13 : 2000 < 0.05	0±0.5 % mA	
Spection (Measu KN(SC) (V) 0 (V) /d (V) /a (AC	ement after temperature M3011/6 M3226 M3014 L 1/S4)	e balance of the samples at room Transformation ratio (IP=3' Offset current Test voltage, 1s Partial discharge voltage a	temperature; S 10A, 40-80 F	C = significan Iz)	t characteristic) 13 : 2000 < 0.05 2.5 1500	0 ± 0.5 % mA kVRMS	
Spection (Measu K _N (SC) (V) 0 (V) /d (V) /e (AC	ement after temperature M3011/6 M3226 M3014 L 1/S4)	e balance of the samples at room Transformation ratio (IP=3' Offset current Test voltage, 1s Partial discharge voltage a with V _{vor}	temperature; S 10A, 40-80 F cc. M3024	C = significan Iz)	t characteristic) 13 : 2000 < 0.05 2.5 1500 1875	0 ± 0.5 % mA kVRMS VRMS VRMS VRMS	
spection (Measu KN(SC) (V) 0 (V) /d (V) /e (AC pe Testing (Prec	ement after temperature M3011/6 M3226 M3014 L 1/S4) ondition acc. to M3236)	e balance of the samples at room Transformation ratio (IP=3' Offset current Test voltage, 1s Partial discharge voltage a with V _{vor}	temperature; S 10A, 40-80 F cc. M3024	C = significan Iz)	t characteristic) 13 : 2000 < 0.05 2.5 1500 1875	0±0.5 % mA kVrms Vrms Vrms Vrms	
spection (Measu ⟨N(SC) (V) ₀ (V) √d (V) √e (AC pe Testing (Prec √w (Prec	ement after temperature M3011/6 M3226 M3014 L 1/S4) andition acc. to M3236) HV transient test a 5 pulse → polarity	e balance of the samples at room Transformation ratio (IP=3' Offset current Test voltage, 1s Partial discharge voltage a with V _{vor} according to M3064 (1,2 μs / 5 γ +, 5 pulse → polarity -	temperature; S 10A, 40-80 F cc. M3024 0 μs-wave fo	C = significan Iz) rm)	t characteristic) 13 : 2000 < 0.05 2.5 1500 1875 8	0 ± 0.5 % mA kVrms Vrms Vrms kV	
Spection (Measu KN(SC) (V) 0 (V) /d (V) /e (AC pe Testing (Prec /w /d	ement after temperature M3011/6 M3226 M3014 L 1/S4) ondition acc. to M3236) HV transient test a 5 pulse → polarity Testing voltage ac	e balance of the samples at room Transformation ratio (IP=3* Offset current Test voltage, 1s Partial discharge voltage a with V _{vor} according to M3064 (1,2 μs / 5 γ +, 5 pulse → polarity - cc. M3014	temperature; S 10A, 40-80 F cc. M3024 0 μs-wave fo	C = significan Iz) rm) (5s)	t characteristic) 13 : 2000 < 0.05 2.5 1500 1875 8 5	0±0.5 % mA kVrms Vrms Vrms kV kV	
Spection (Measu KN(SC) (V) 0 (V) /d (V) /e (AC pe Testing (Prec /w //d /e (Prec	ement after temperature M3011/6 M3226 M3014 L 1/S4) ondition acc. to M3236) HV transient test a 5 pulse → polarity Testing voltage ac Partial discharge v	e balance of the samples at room Transformation ratio (IP=3 ³ Offset current Test voltage, 1s Partial discharge voltage a with V _{vor} according to M3064 (1,2 μs / 5 (+, 5 pulse → polarity - cc. M3014 voltage acc. M3024	temperature; S 10A, 40-80 F cc. M3024 0 μs-wave fo	C = significan Iz) rm) (5s)	t characteristic) 13 : 2000 < 0.05 2.5 1500 1875 8 5 1500	0 ± 0.5 % mA kVrms Vrms Vrms kV kVrms Vrms	



The offset ripple can be reduced by an external low pass. Simplest solution is a passive low pass filter of 1st order with

 $f_g = \frac{1}{2\pi \cdot R_M \cdot C_s}$

In this case the response time is enlarged. It is calculated from:

$$t'_r \leq t_r + 2,5R_MC_a$$

Applicable documents

Temperature of the primary conductor should not exceed 105°C.

Current direction: A positive output current appears at point Is, by primary current in direction of the arrow.

Constructed and manufactored and tested in accordance with EN 61800.

Further standards UL 508 ; file E317483, category NMTR2 / NMTR8

"The color of the plastic material is not specified and the current sensor can be supplied in different colors

(e.g. brown, black, white, natural). This has no effect on the specifications or UL approval.'

Hrsg.: R&D-PD NPI D editor	Bearb: DJ designer	MC-PM: NSch.		freig.: SB released

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